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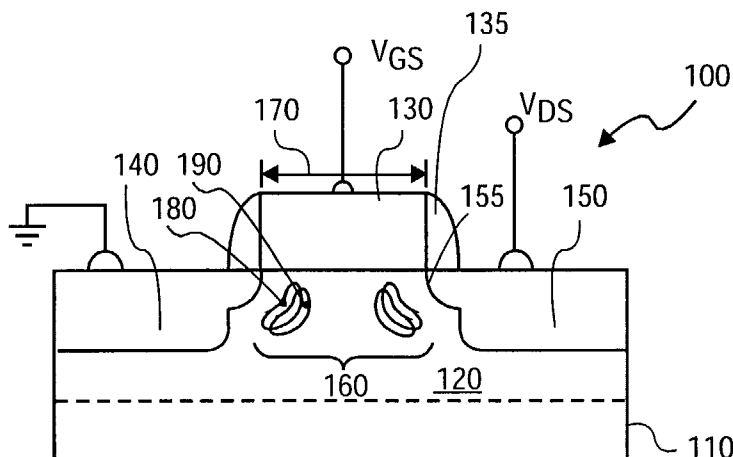
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(54) Title: INDIUM-BORON DUAL HALO FOR MOSFET



(57) Abstract: A method including forming a transistor device having a channel region; implanting a first halo into the channel region; and implanting a second different halo into the channel region. An apparatus including a gate electrode formed on a substrate; a channel region formed in the substrate below the gate electrode and between contact points; a first halo implant comprising a first species in the channel region; and a second halo implant including a different second species in the channel region.